

MICROWAVE NPN POWER TRANSISTOR FOR CLASS C OPERATION
TRANSISTOR NPN HYPERFREQUENCE DE PUISSANCE, CLASSE C
FEATURES

- Gold metallizations
 - Glass passivated structure
 - Hermetical ceramic package
 - Emitter ballast resistors
 - Auto-aligned structure
- } → high reliability
- severe impedance mismatch
- high characteristics
- reproducibility

APPLICATIONS

Telecommunications up to 1 GHz frequency band.

PARTICULARITES

- Métallisations "Or"
 - Structure passivée
 - Boîtier céramique hermétique
 - Résistances ballast d'émetteur
 - Structure auto-alignée
- } → haute fiabilité
- bonne tenue au ROS
- bonne reproductibilité des caractéristiques

APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 1 GHz

$f = 1 \text{ GHz}$

$P_{OUT} = 2 \text{ W}$

$G_P = 10 \text{ dB}$

$\eta_c = 50 \%$

$V_{CC} = 28 \text{ V}$


 Case : CB-294 (.2502LFL/FLM)
 Boîtier : CB-311 (.2502L/2LM)

ABSOLUTE RATINGS (LIMITING VALUES)
VALEURS LIMITES ABSOLUES D'UTILISATION

	Symbols	Values	Units
Emitter-base (d.c.) voltage <i>Tension continue émetteur-base</i>	VEBO	3	V
Collector-base (d.c.) voltage <i>Tension continue collecteur-base</i>	VCBO	45	V
Collector-emitter (d.c.) voltage <i>Tension continue collecteur-émetteur</i>	VCES	45	V
Collector (d.c.) current <i>Courant continu de collecteur</i>	IC	0,4	A
Storage and junction temperature range <i>Températures extrêmes de stockage et de jonction</i>	T _{stg} T _j	— 65 → + 200 — 55 → + 200	°C °C

 Thermal resistance (junction-case)
Résistance thermique (jonction-boîtier)

 R_{th(j-c)}

20

°C/W

October 1980 - 1/4

STATIC CHARACTERISTICS at $t_{amb} = 25^{\circ}\text{C}$
CARACTERISTIQUES STATIQUES à $t_{amb} = 25^{\circ}\text{C}$

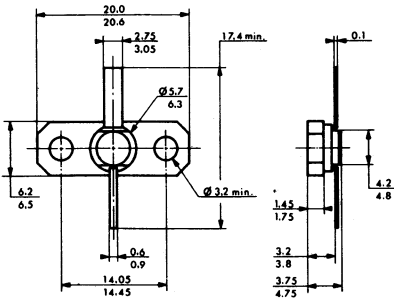
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
V(BR)EBO	3			V	$I_E = 1\text{ mA}$
V(BR)CBO	45			V	$I_C = 10\text{ mA}$
V(BR)CES	45			V	$I_C = 10\text{ mA}$
I_{CBO}			1	mA	$V_{CB} = 28\text{ V}$
HFE	10		120		$I_C = 100\text{ mA}$ $V_{CE} = 5\text{ V}$
C22b			3	pF	$V_{CB} = 28\text{ V}$ $f = 1\text{ MHz}$

DYNAMIC CHARACTERISTICS at $t_{amb} = 25^{\circ}\text{C}$
CARACTERISTIQUES DYNAMIQUES à $t_{amb} = 25^{\circ}\text{C}$

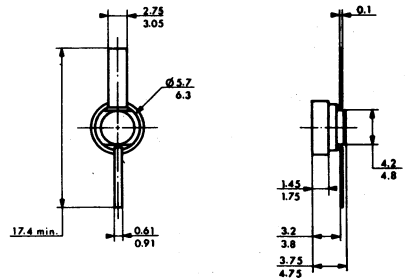
Symbols	Values			Units	Test conditions		
	min.	typ.	max.				
P_{OUT}	1,8	2		W	$f = 1\text{ GHz}$	$V_{CC} = 28\text{ V}$	$P_{IN} = 0,2\text{ W}$
Gp	9,5	10		dB	$f = 1\text{ GHz}$	$V_{CC} = 28\text{ V}$	$P_{IN} = 0,2\text{ W}$
η_c	45	50		%	$f = 1\text{ GHz}$	$V_{CC} = 28\text{ V}$	$P_{IN} = 0,2\text{ W}$

CASE DESCRIPTION
DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM)
 BMH 75 a



CB-311 (.2502L/2LM)
 BMH 75 b



Dimensions in millimeters

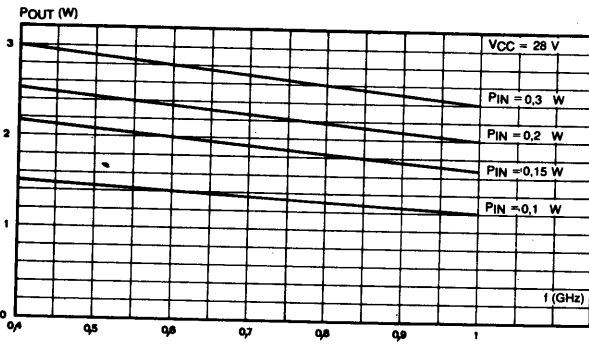


Fig. 1 - Output power versus frequency (typical values).

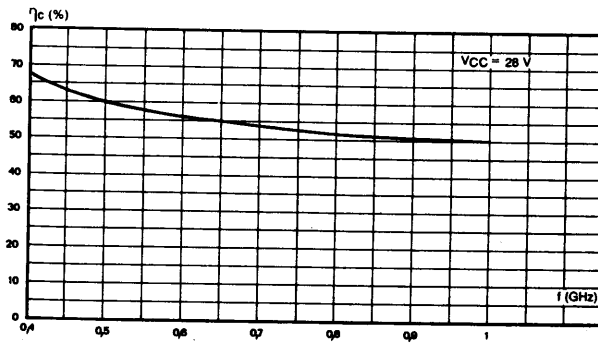


Fig. 2 - Collector efficiency versus frequency (typical values).

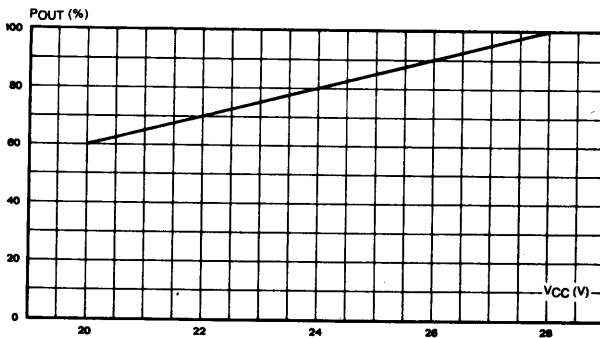


Fig. 3 - Relative output power versus collector voltage.

Z_{IN} : Input impedance
 Z_{CL} : Collector load impedance

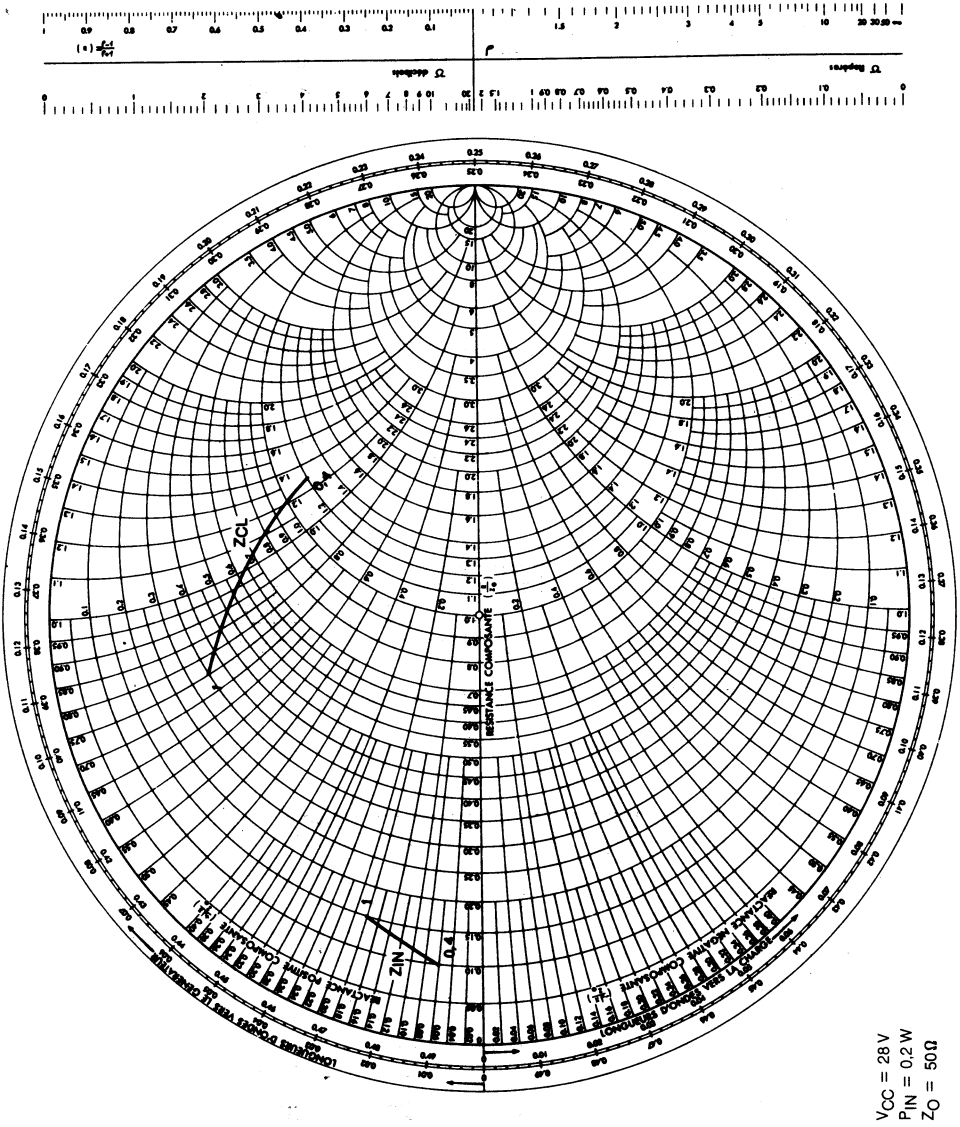


Fig. 4 - Smith chart

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APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 1 GHz

$$f = 1 \text{ GHz}$$

$$P_{OUT} = 6,6 \text{ W}$$

$$GP = 11,2 \text{ dB}$$

$$\eta_c = 52 \%$$

$$V_{CC} = 28 \text{ V}$$


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ABSOLUTE RATINGS (LIMITING VALUES)
VALEURS LIMITES ABSOLUES D'UTILISATION

	Symbols	Values	Units
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Collector (d.c.) current <i>Courant continu de collecteur</i>	IC	1,2	A
Storage and junction temperature range <i>Températures extrêmes de stockage et de jonction</i>	T _{stg} T _j	— 65 → + 200 — 55 → + 200	°C °C

 Thermal resistance (junction-case)
Résistance thermique (jonction-boîtier)

 R_{th(j-c)} 8 °C/W

October 1980 - 1/4

STATIC CHARACTERISTICS at $t_{amb} = 25^{\circ}\text{C}$
CARACTERISTIQUES STATIQUES à $t_{amb} = 25^{\circ}\text{C}$

Symbols	Values			Units	Test conditions
	min.	typ.	max.		
V(BR)EBO	3			V	IE = 3 mA
V(BR)CBO	45			V	IC = 30 mA
V(BR)CES	45			V	IC = 30 mA
ICBO			3	mA	V _{CB} = 28 V
HFE	10		120		IC = 250 mA V _{CE} = 5 V
C22b			5,5	pF	V _{CB} = 28 V f = 1 MHz

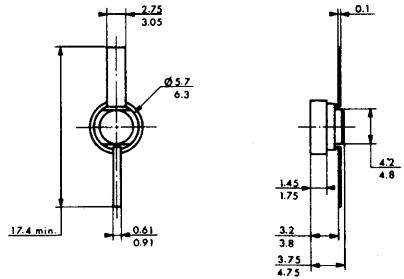
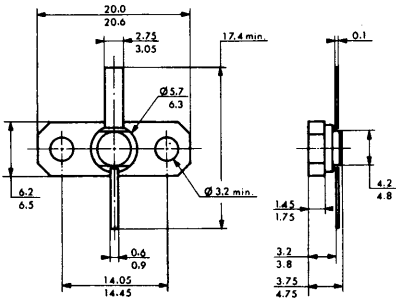
DYNAMIC CHARACTERISTICS at $t_{amb} = 25^{\circ}\text{C}$
CARACTERISTIQUES DYNAMIQUES à $t_{amb} = 25^{\circ}\text{C}$

Symbols	Values			Units	Test conditions
	min.	typ.	max.		
POUT	5	6,6		W	f = 1 GHz V _{CC} = 28 V PIN = 0,5 W
GP	10	11,2		dB	f = 1 GHz V _{CC} = 28 V PIN = 0,5 W
η_c	50	52		%	f = 1 GHz V _{CC} = 28 V PIN = 0,5 W

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DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM)
 BMH 75 a

CB-311 (.2502L2LM)
 BMH 75 b



Dimensions in millimeters

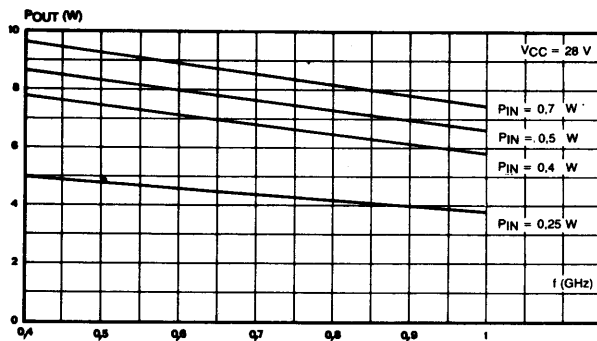


Fig. 1 - Output power versus frequency (typical values).

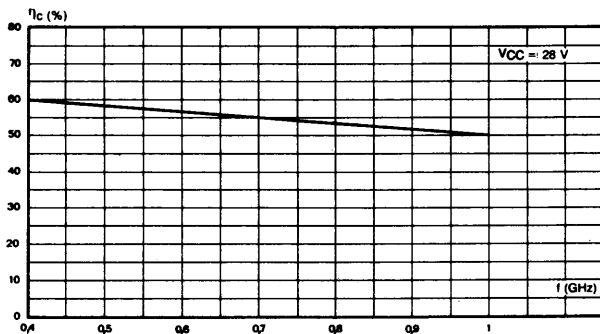


Fig. 2 - Collector efficiency versus frequency (typical values).

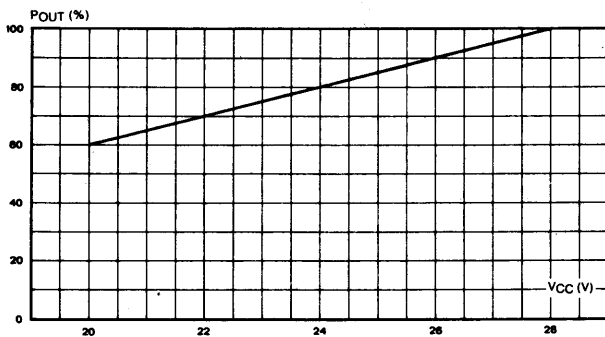
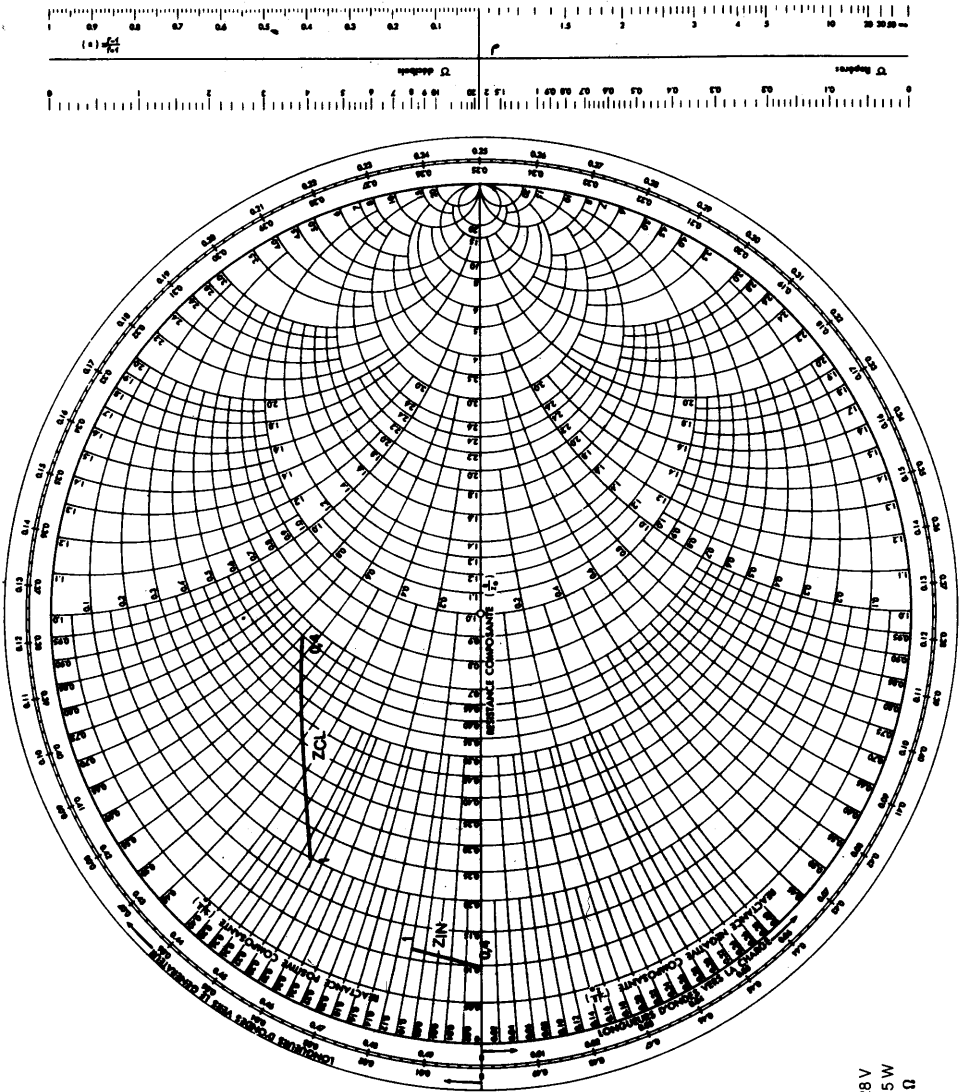


Fig. 3 - Relative output power versus collector voltage.

Z_{IN} : Input impedance
 Z_{CL} : Collector load impedance



$V_{CC} = 28V$
 $P_{IN} = 0.5W$
 $Z_0 = 50\Omega$

Fig. 4 - Smith chart

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APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 1 GHz

$$f = 1 \text{ GHz}$$

$$POUT = 12 \text{ W}$$

$$GP = 10,8 \text{ dB}$$

$$\eta_c = 64 \%$$

$$V_{CC} = 28 \text{ V}$$



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ABSOLUTE RATINGS (LIMITING VALUES) VALEURS LIMITES ABSOLUES D'UTILISATION

	Symbols	Values	Units
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Collector-base (d.c.) voltage <i>Tension continue collecteur-base</i>	VCBO	45	V
Collector-emitter (d.c.) voltage <i>Tension continue collecteur-émetteur</i>	VCES	45	V
Collector (d.c.) current <i>Courant continu de collecteur</i>	IC	2	A
Storage and junction temperature range <i>Températures extrêmes de stockage et de jonction</i>	T _{stg} T _j	— 65 → + 200 — 55 → + 200	°C °C

Thermal resistance (junction-case)
Résistance thermique (jonction-boîtier)

R_{th(j-c)}

5

°C/W

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STATIC CHARACTERISTICS at $t_{amb} = 25^{\circ}\text{C}$
CARACTERISTIQUES STATIQUES à $t_{amb} = 25^{\circ}\text{C}$

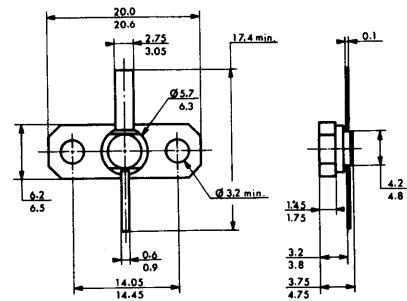
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
V(BR)EBO	3			V	IE = 5 mA
V(BR)CBO	45			V	IC = 50 mA
V(BR)CES	45			V	IC = 50 mA
ICBO			5	mA	VCB = 28 V
HFE	10		120		IC = 500 mA VCE = 5 V
C22b			8	pF	VCB = 28 V f = 1 MHz

DYNAMIC CHARACTERISTICS at $t_{amb} = 25^{\circ}\text{C}$
CARACTERISTIQUES DYNAMIQUES à $t_{amb} = 25^{\circ}\text{C}$

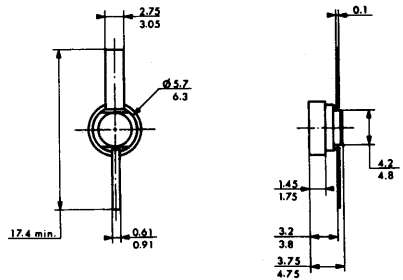
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
POUT	10	12		W	f = 1 GHz VCC = 28 V PIN = 1 W
Gp	10	10,8		dB	f = 1 GHz VCC = 28 V PIN = 1 W
η_c	60	64		%	f = 1 GHz VCC = 28 V PIN = 1 W

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 BMH 75 a



CB-311 (.2502L/2LM)
 BMH 75 b



Dimensions in millimeters

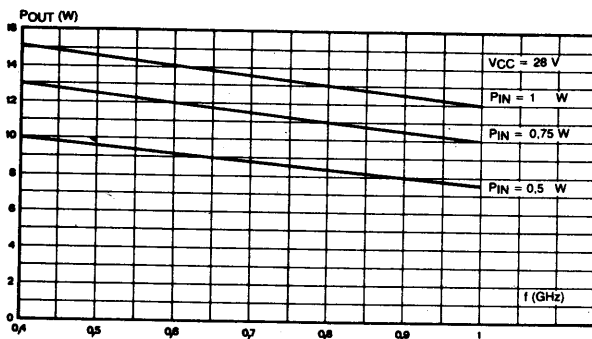


Fig. 1 - Output power versus frequency (typical values).

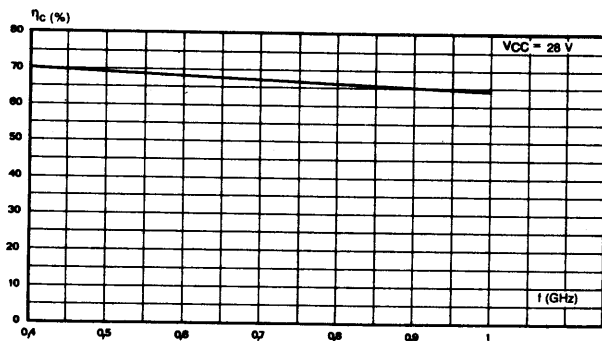


Fig. 2 - Collector efficiency versus frequency (typical values).

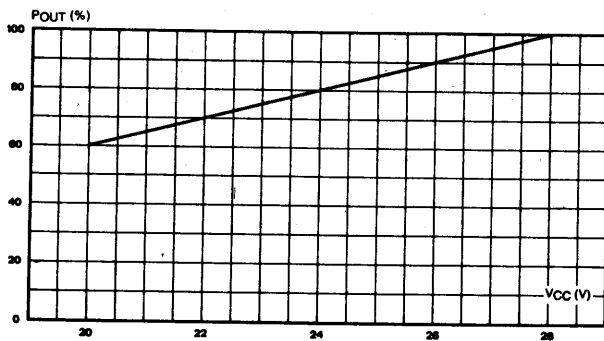


Fig. 3 - Relative output power versus collector voltage.

Z_{IN} : Input impedance
 Z_{CL} : Collector load impedance

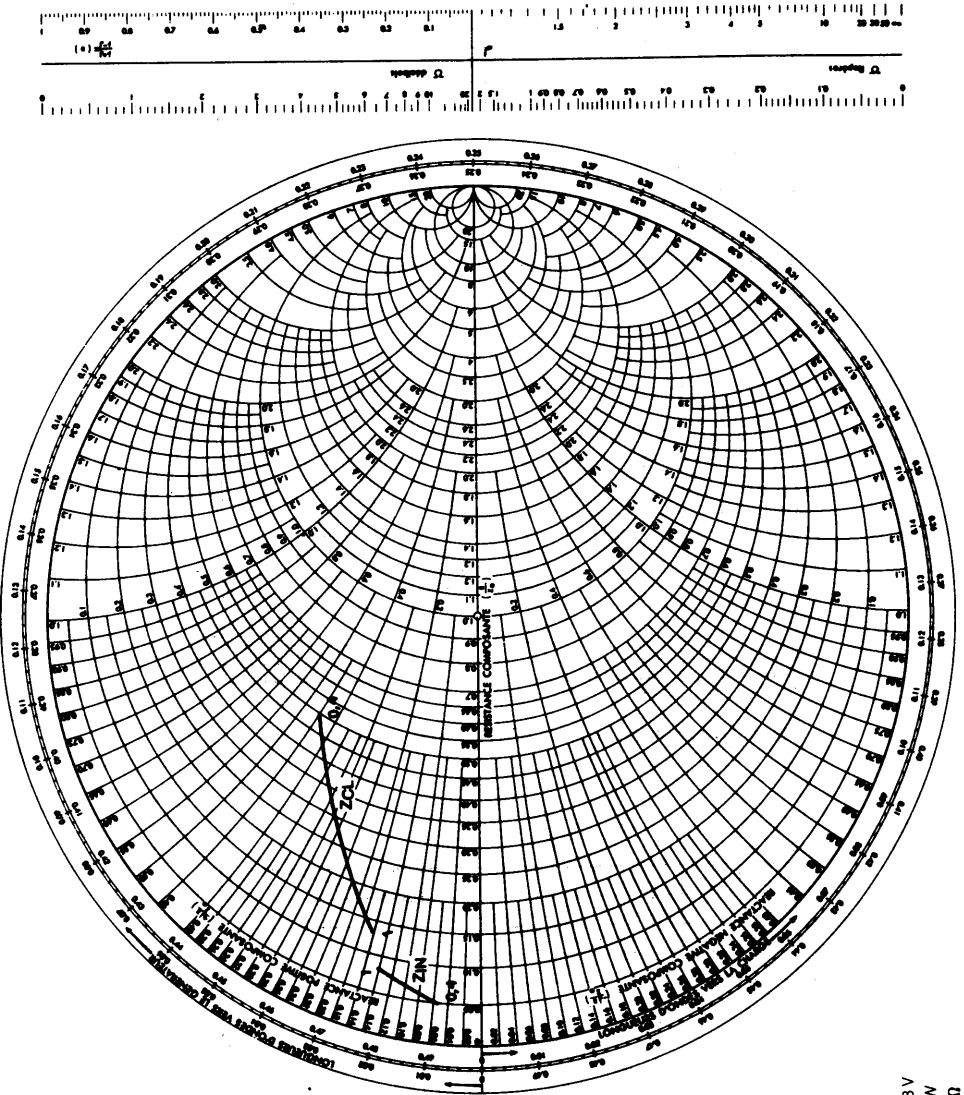


Fig. 4. Smith chart

$V_{CC} = 28V$
 $P_{IN} = 1W$
 $Z_0 = 50\Omega$

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Telecommunications up to 2 GHz frequency band.

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APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 2 GHz

$f = 2 \text{ GHz}$

$P_{OUT} = 1,1 \text{ W}$

$G_P = 7,4 \text{ dB}$

$\eta_c = 40 \%$

$V_{CC} = 28 \text{ V}$



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ABSOLUTE RATINGS (LIMITING VALUES)
VALEURS LIMITES ABSOLUES D'UTILISATION

	Symbols	Values	Units
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Collector-emitter (d.c.) voltage <i>Tension continue collecteur-émetteur</i>	VCES	45	V
Collector (d.c.) current <i>Courant continu de collecteur</i>	I _C	0,4	A
Storage and junction temperature range <i>Températures extrêmes de stockage et de jonction</i>	T _{stg} T _j	- 65 → + 200 - 55 → + 200	°C °C

Thermal resistance (junction-case)
Résistance thermique (jonction-boîtier)

R _{th(j-c)}	20	°C/W
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February 1981 - 1/4

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STATIC CHARACTERISTICS at $t_{amb} = 25^{\circ}\text{C}$
 CARACTERISTIQUES STATIQUES à $t_{amb} = 25^{\circ}\text{C}$

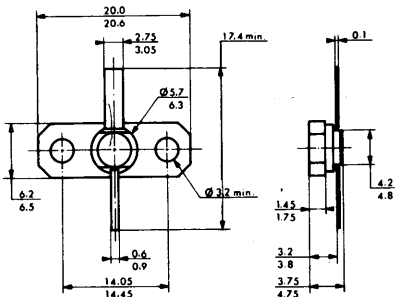
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
$V_{(BR)EBO}$	3			V	$I_E = 1 \text{ mA}$
$V_{(BR)CBO}$	45			V	$I_C = 10 \text{ mA}$
$V_{(BR)CES}$	45			V	$I_C = 10 \text{ mA}$
I_{CBO}			1	mA	$V_{CB} = 28 \text{ V}$
HFE	10		120		$I_C = 100 \text{ mA}$ $V_{CE} = 5 \text{ V}$
C_{22b}			3	pF	$V_{CB} = 28 \text{ V}$ $f = 1 \text{ MHz}$

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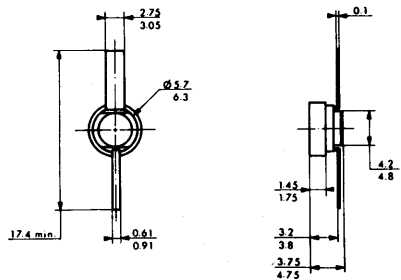
Symbols	Values			Units	Test conditions		
	min.	typ.	max.				
P_{OUT}	1	1,1		W	$f = 2 \text{ GHz}$	$V_{CC} = 28 \text{ V}$	$P_{IN} = 0,2 \text{ W}$
GP	7	7,4		dB	$f = 2 \text{ GHz}$	$V_{CC} = 28 \text{ V}$	$P_{IN} = 0,2 \text{ W}$
η_c	37	40		%	$f = 2 \text{ GHz}$	$V_{CC} = 28 \text{ V}$	$P_{IN} = 0,2 \text{ W}$

CASE DESCRIPTION
 DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM)
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CB-311 (.2502L2LM)
 BMH 75 b



Dimensions in millimeters

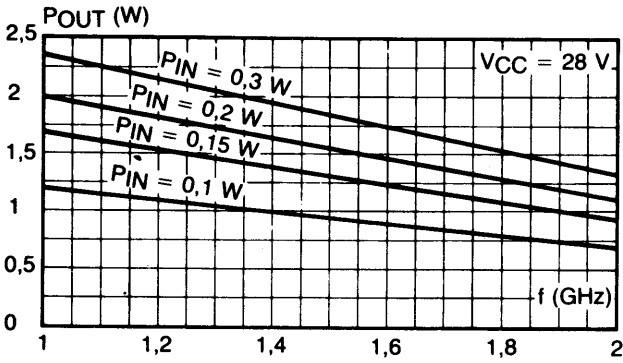


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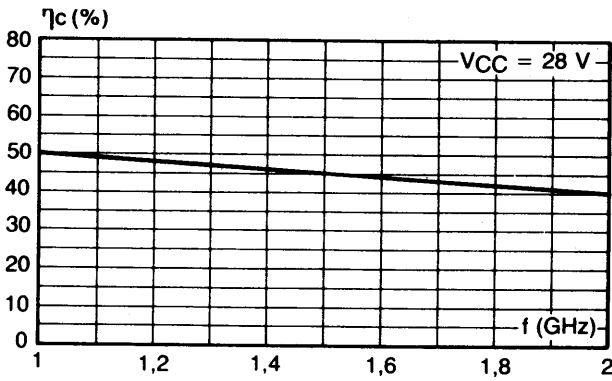


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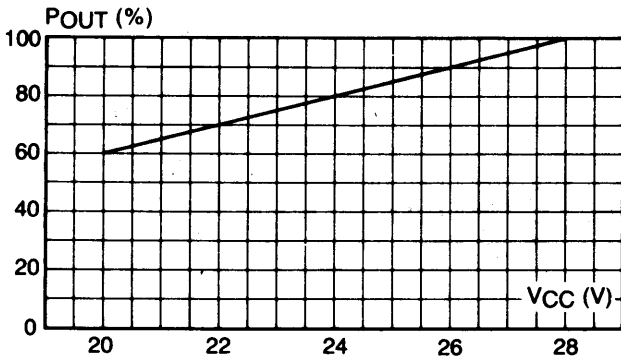


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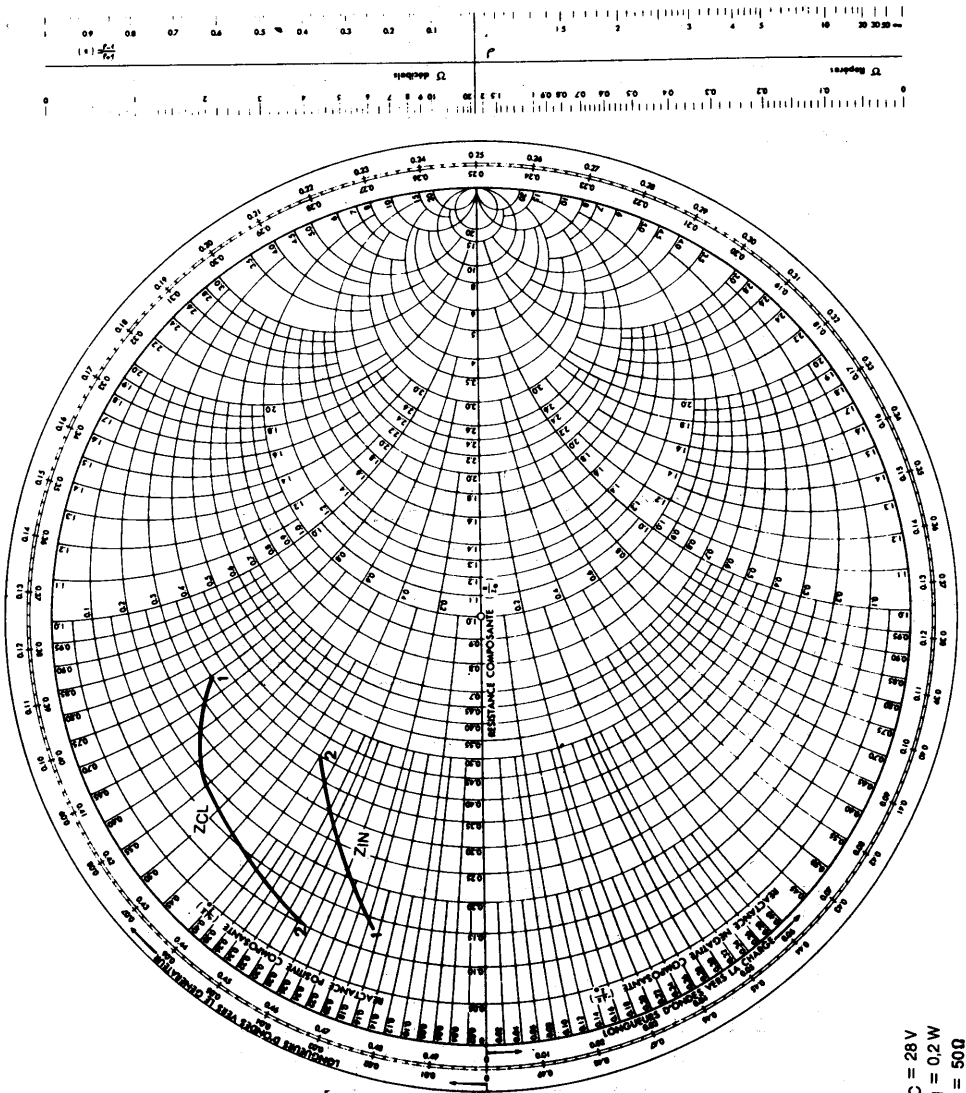


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Télécommunications dans la bande de fréquences jusqu'à 2 GHz

$$f = 2 \text{ GHz}$$

$$P_{OUT} = 3,3 \text{ W}$$

$$GP = 8,2 \text{ dB}$$

$$\eta_c = 40 \%$$

$$V_{CC} = 28 \text{ V}$$


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Résistance thermique (jonction-boîtier)

 R_{th(j-c)}

8

°C/W

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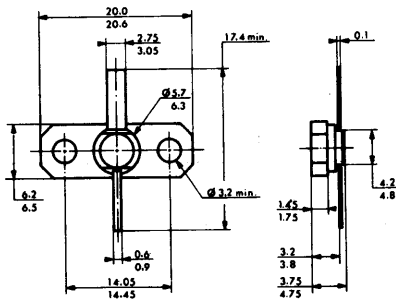
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I _{CBO}			3	mA	$V_{CB} = 28 \text{ V}$
h _{FE}	10		120		$I_C = 250 \text{ mA}$ $V_{CE} = 5 \text{ V}$
C _{22b}			5,5	pF	$V_{CB} = 28 \text{ V}$ $f = 1 \text{ MHz}$

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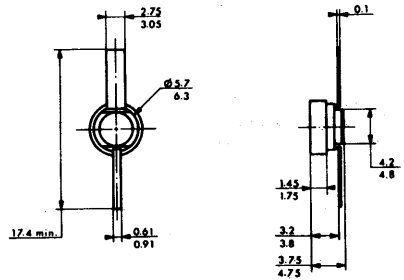
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G _p	7,8	8,2		dB	$f = 2 \text{ GHz}$ $V_{CC} = 28 \text{ V}$ $P_{IN} = 0,5 \text{ W}$
η_c	37	40		%	$f = 2 \text{ GHz}$ $V_{CC} = 28 \text{ V}$ $P_{IN} = 0,5 \text{ W}$

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 (BMH 75 b)



Dimensions in millimeters

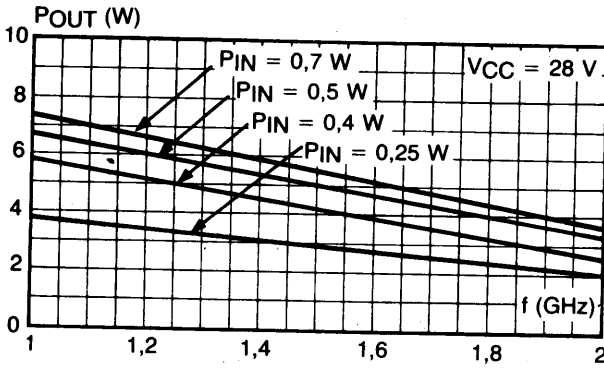


Fig. 1 - Output power versus frequency (typical values).

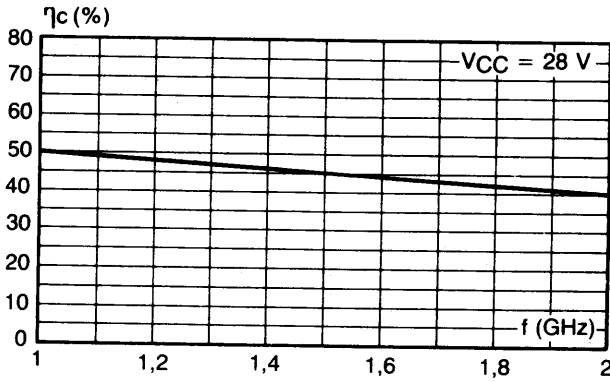


Fig. 2 - Collector efficiency versus frequency (typical values).

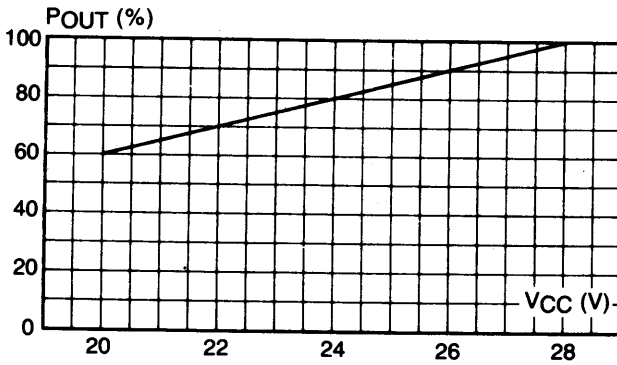
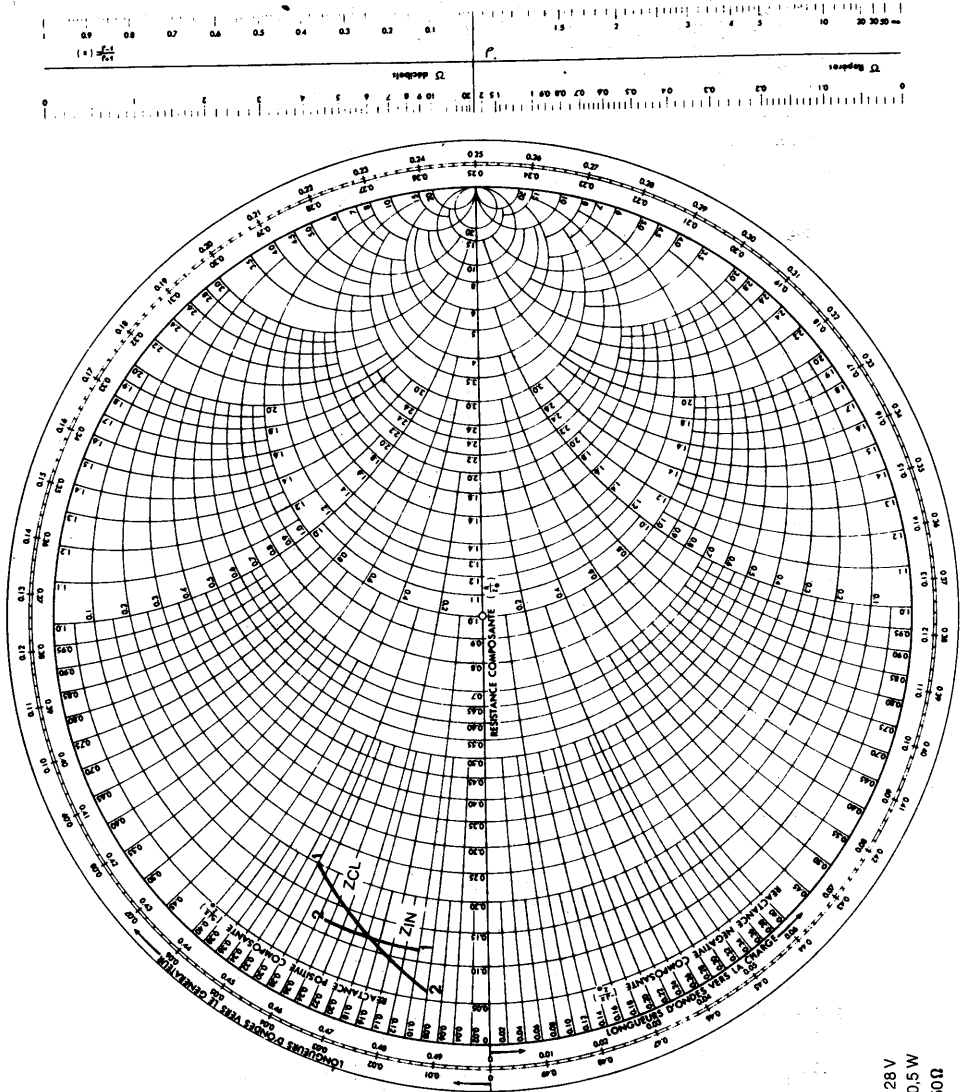


Fig. 3 - Relative output power versus collector voltage.

Z_{IN} : Input impedance
 Z_{CL} : Collector load impedance



$V_{CC} = 28V$
 $P_{IN} = 0.5W$
 $Z_0 = 50\Omega$

Fig. 4 - Smith chart

**MICROWAVE NPN POWER TRANSISTOR FOR CLASS C OPERATION
TRANSISTOR NPN HYPERFREQUENCE DE PUISSANCE, CLASSE C****FEATURES**

- Gold metallizations
 - Glass passivated structure
 - Hermetic ceramic package
 - Emitter ballast resistors
 - Auto-aligned structure
- } → high reliability
- severe impedance mismatch
- high characteristics reproductibility

APPLICATIONS

Telecommunications up to 2 GHz frequency band.

PARTICULARITES

- Métallisations "Or"
 - Structure passivée
 - Boîtier céramique hermétique
 - Résistances ballast d'émetteur
 - Structure auto-alignée
- } → haute fiabilité
- bonne tenue au ROS
- bonne reproductibilité des caractéristiques

APPLICATIONS

Télécommunications dans la bande de fréquences jusqu'à 2 GHz

$f = 2 \text{ GHz}$

$POUT = 5,5 \text{ W}$

$GP = 7,4 \text{ dB}$

$\eta_c = 40 \%$

$V_{CC} = 28 \text{ V}$



Case : CB-294 (.2502LFL/FLM)
Boîtier : CB-311 (.2502L/2LM)

**ABSOLUTE RATINGS (LIMITING VALUES)
VALEURS LIMITES ABSOLUES D'UTILISATION**

	Symbols	Values	Units
Emitter-base (d.c.) voltage <i>Tension continue émetteur-base</i>	VEBO	3	V
Collector-base (d.c.) voltage <i>Tension continue collecteur-base</i>	VCBO	45	V
Collector-emitter (d.c.) voltage <i>Tension continue collecteur-émetteur</i>	VCES	45	V
Collector (d.c.) current <i>Courant continu de collecteur</i>	IC	2	A
Storage and junction temperature range <i>Températures extrêmes de stockage et de jonction</i>	T _{stg} T _j	— 65 → + 200 — 55 → + 200	°C °C

Thermal resistance (junction-case)
Résistance thermique (jonction-boîtier)

R_{th(j-c)}

5

°C/W

February 1981 - 1/4

STATIC CHARACTERISTICS at $t_{amb} = 25^{\circ}\text{C}$
CARACTERISTIQUES STATIQUES à $t_{amb} = 25^{\circ}\text{C}$

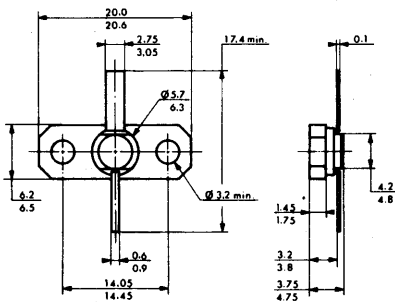
Symbols	Values			Units	Test conditions
	min.	typ.	max.		
$V_{(BR)EBO}$	3			V	$I_E = 5 \text{ mA}$
$V_{(BR)CBO}$	45			V	$I_C = 50 \text{ mA}$
$V_{(BR)CES}$	45			V	$I_C = 50 \text{ mA}$
I_{CBO}			5	mA	$V_{CB} = 28 \text{ V}$
HFE	10		120		$I_C = 500 \text{ mA}$ $V_{CE} = 5 \text{ V}$
C22b			8	pF	$V_{CB} = 28 \text{ V}$ $f = 1 \text{ MHz}$

DYNAMIC CHARACTERISTICS at $t_{amb} = 25^{\circ}\text{C}$
CARACTERISTIQUES DYNAMIQUES à $t_{amb} = 25^{\circ}\text{C}$

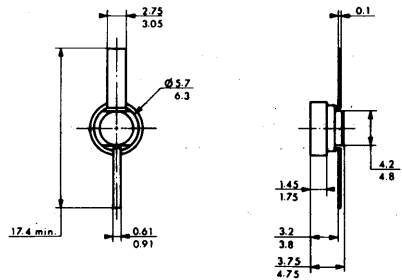
Symbols	Values			Units	Test conditions		
	min.	typ.	max.				
P_{OUT}	5	5,5		W	$f = 2 \text{ GHz}$	$V_{CC} = 28 \text{ V}$	$P_{IN} = 1 \text{ W}$
Gp	7	7,4		dB	$f = 2 \text{ GHz}$	$V_{CC} = 28 \text{ V}$	$P_{IN} = 1 \text{ W}$
η_c	37	40		%	$f = 2 \text{ GHz}$	$V_{CC} = 28 \text{ V}$	$P_{IN} = 1 \text{ W}$

CASE DESCRIPTION
DESCRIPTION DU BOITIER

CB-294 (.2502LFL/FLM)
 (BMH 75 a)



CB-311 (.2502L/2LM)
 (BMH 75 b)



Dimensions in millimeters

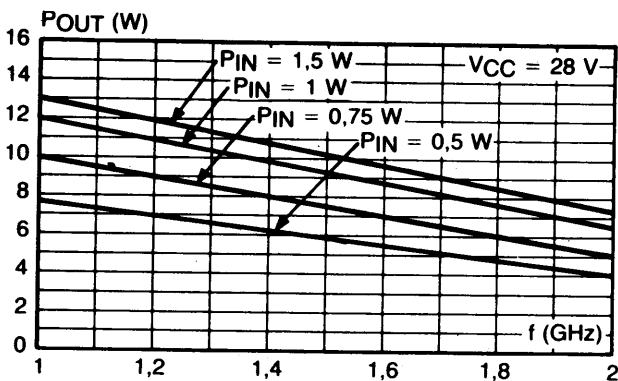


Fig. 1 - Output power versus frequency (typical values).

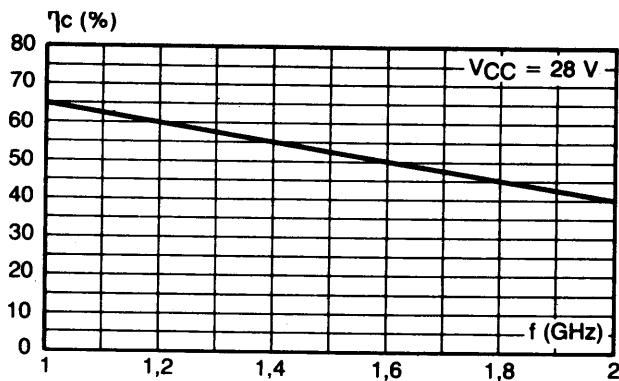


Fig. 2 - Collector efficiency versus frequency (typical values).

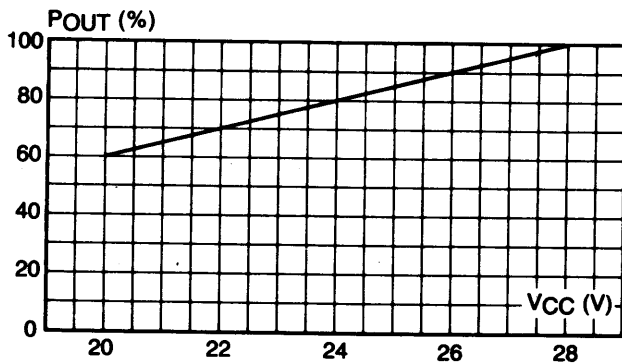


Fig. 3 - Relative output power versus collector voltage.

Z_{IN} : Input impedance
 Z_{CL} : Collector load impedance

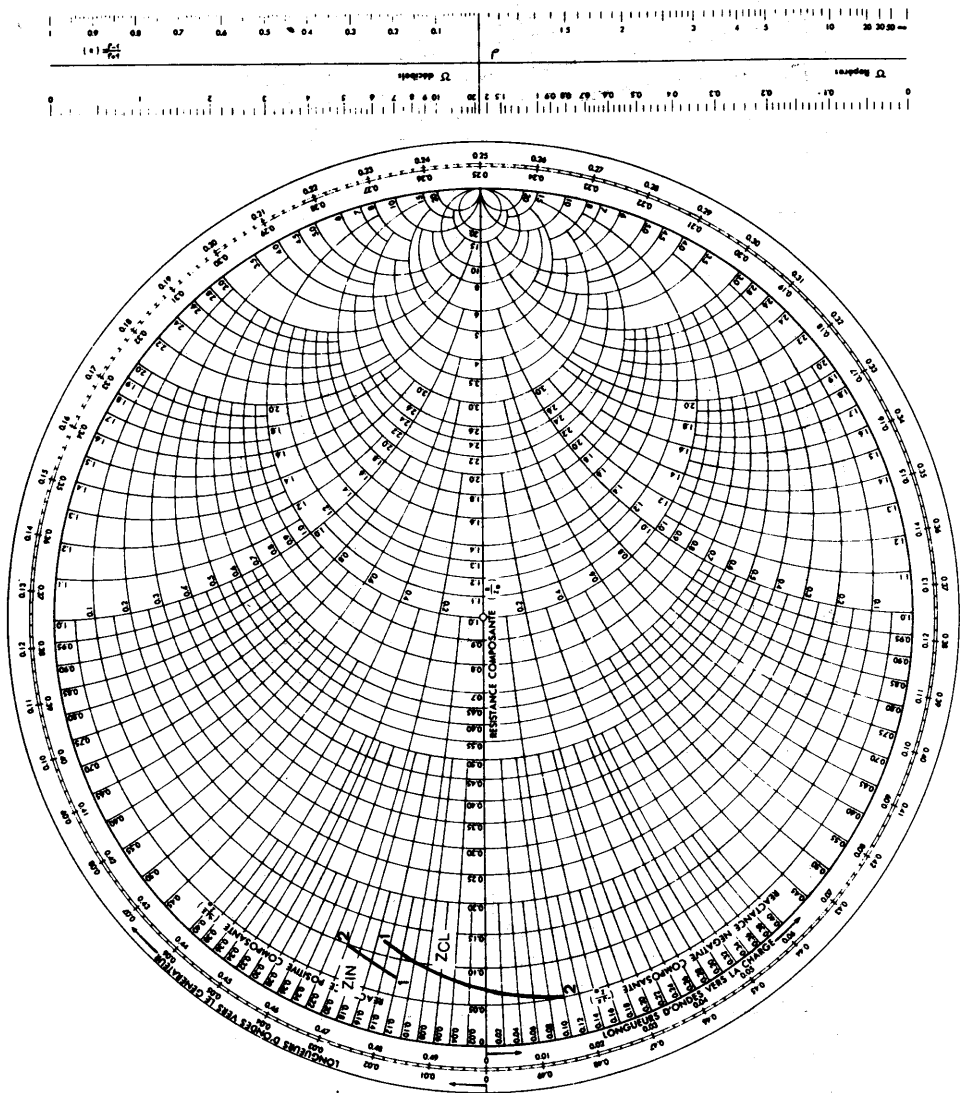


Fig. 4 - Smith chart

$V_{CC} = 28V$
 $P_{IN} = 1W$
 $Z_0 = 50\Omega$